

|   | Document ID   | Issue Date | Pages | Title  | Current OR | Current XRef   | Inventor                       |
|---|---------------|------------|-------|--|------------|--|--------------------------------|
| 1 | US 6184582 B1 | 2001/12/20 | 13    | Small electrode for a chalcogenide switching device and method for fabricating same                |            | 257/3 ; 438/244 ; 438/95                             | Reinberg, Alan R. et al.       |
| 2 | US 6153890 A  | 2000/11/28 | 19    | Memory cell incorporating a chalcogenide element   | 257/3      | 257/2 ; 257/4 ; 257/5                                | Wolstenholme, Graham R. et al. |
| 3 | US 6031287 A  | 2000/02/29 | 24    | Contact structure and memory element incorporating the same  | 257/734    | 257/758 ; 438/622                                    | Harshfield, Steven T.          |
| 4 | US 5751012 A  | 1998/05/12 | 13    | Polysilicon pillar diode for use in a non-volatile memory cell                                     | 257/5      | 257/2 ; 257/209 ; 257/37 ; 257/4 ; 257/530 ; 365/163 | Wolstenholme, Graham R. et al. |
| 5 | US 4177475 A  | 1979/12/04 | 8     | High temperature amorphous memory device for an electrically alterable read-only memory            | 257/2      | 257/616 ; 365/163                                    | Holmberg, Scott H.             |
| 6 | US 4115872 A  | 1978/09/19 | 7     | Amorphous semiconductor memory device for employment in an electrically alterable read-only memory | 365/163    | 257/2  | Bluhm, Vernon A.               |

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